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(19) **United States**(12) **Patent Application Publication****Park et al.**(10) **Pub. No.: US 2002/0167633 A1**(43) **Pub. Date: Nov. 14, 2002**(54) **ARRAY SUBSTRATE FOR IPS MODE
LIQUID CRYSTAL DISPLAY DEVICE AND
METHOD FOR FABRICATING THE SAME**(30) **Foreign Application Priority Data**

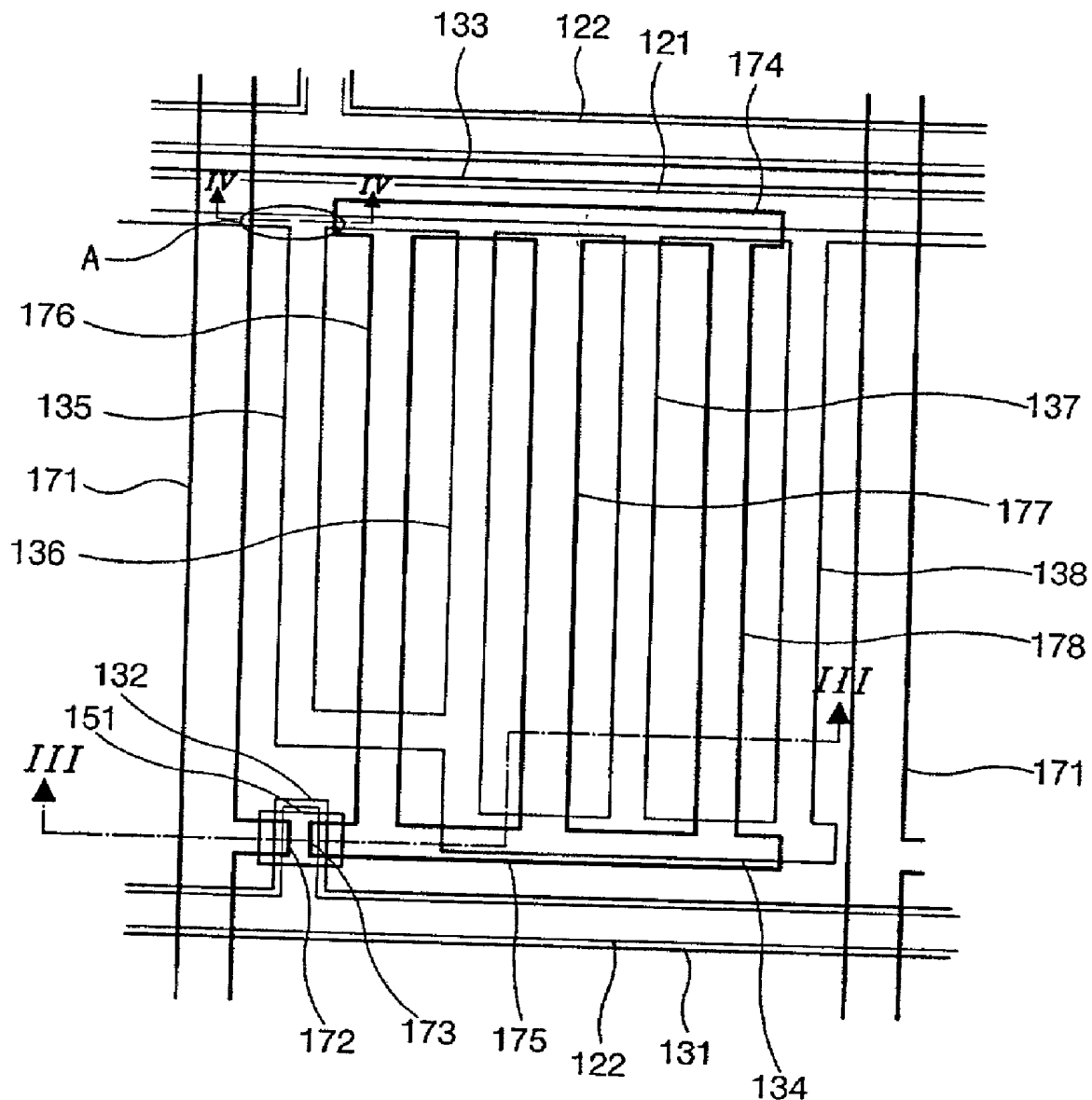
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Gyeongsangbuk-do (KR)**Publication Classification**(51) **Int. Cl.⁷** **G02F 1/1343**(52) **U.S. Cl.** **349/141**

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**MCKENNA LONG & ALDRIDGE LLP
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WASHINGTON, DC 20006 (US)**(57) **ABSTRACT**

An array substrate of in-plane switching (IPS) mode liquid crystal display device includes auxiliary patterns extended from a first conductive line under the common line in order to prevent a short caused by residues of metallic material that is used for forming a data line and the pixel electrode.

(21) Appl. No.: **10/020,894**(22) Filed: **Dec. 19, 2001**

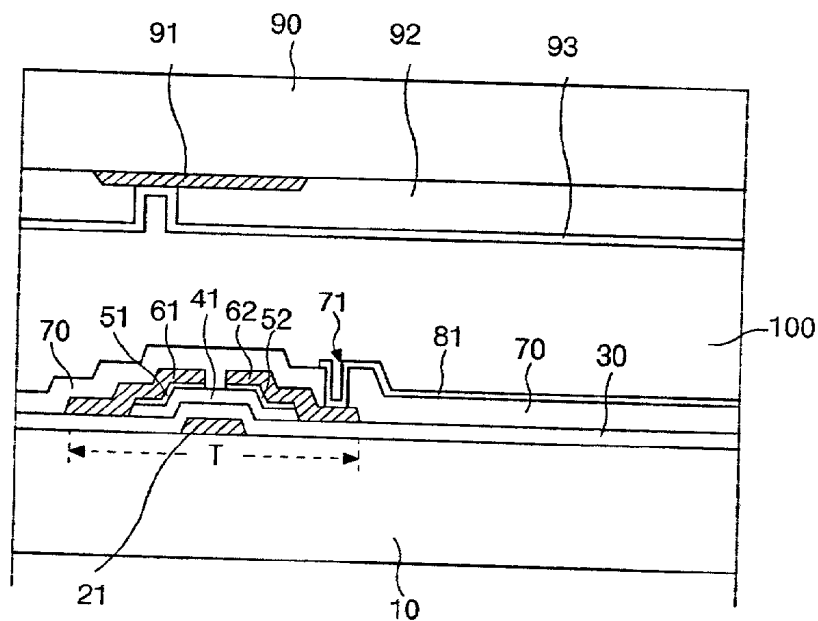


FIG. 1
(RELATED ART)

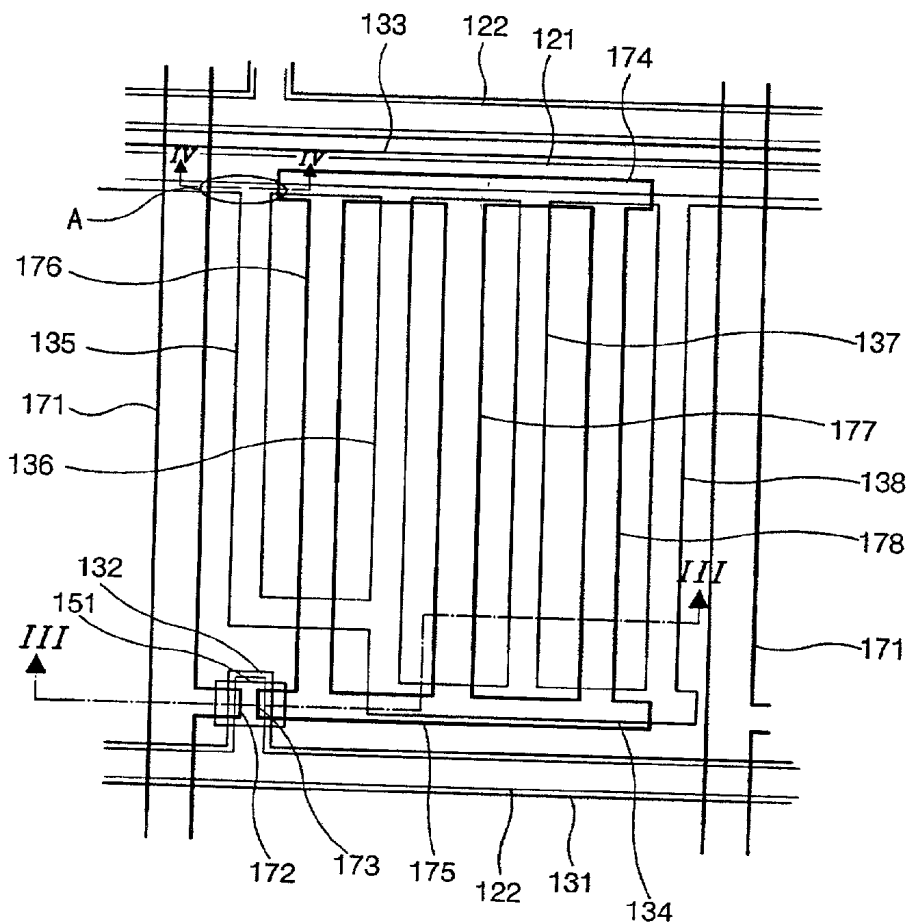


FIG. 2

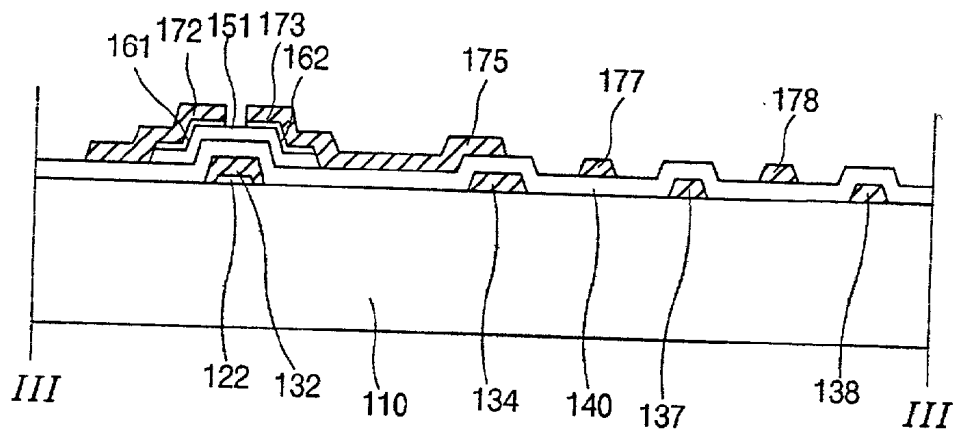


FIG. 3

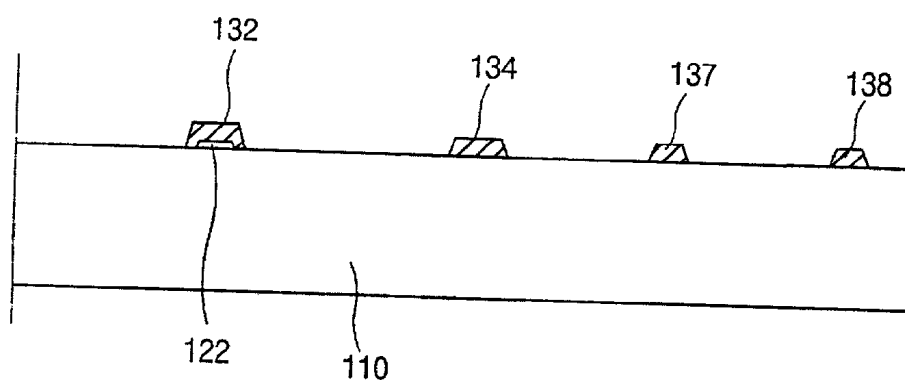


FIG. 4A

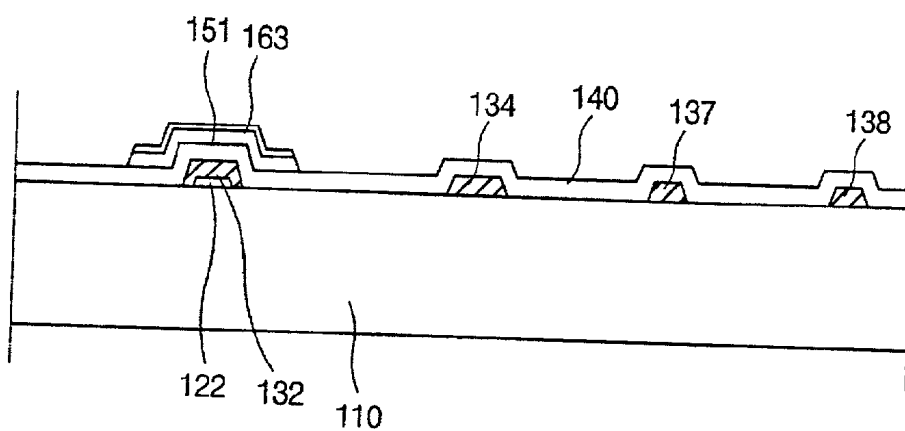


FIG. 4B

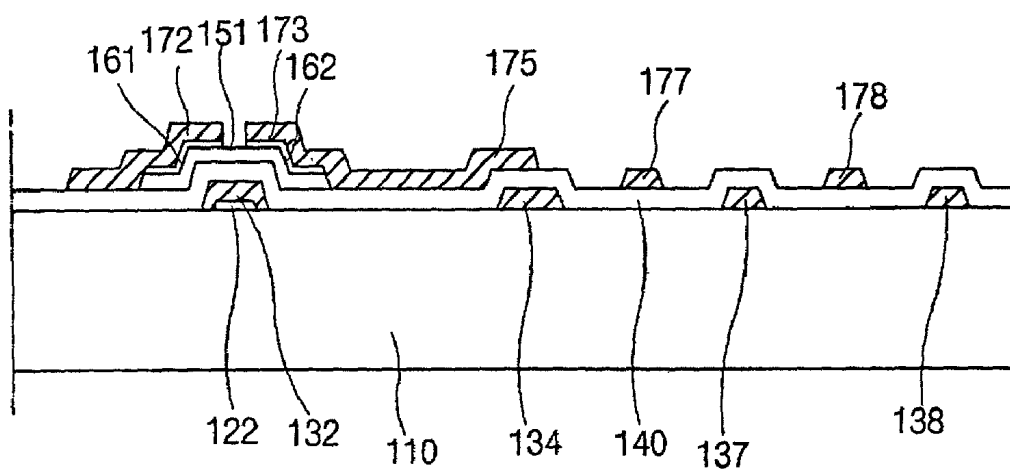


FIG. 4C

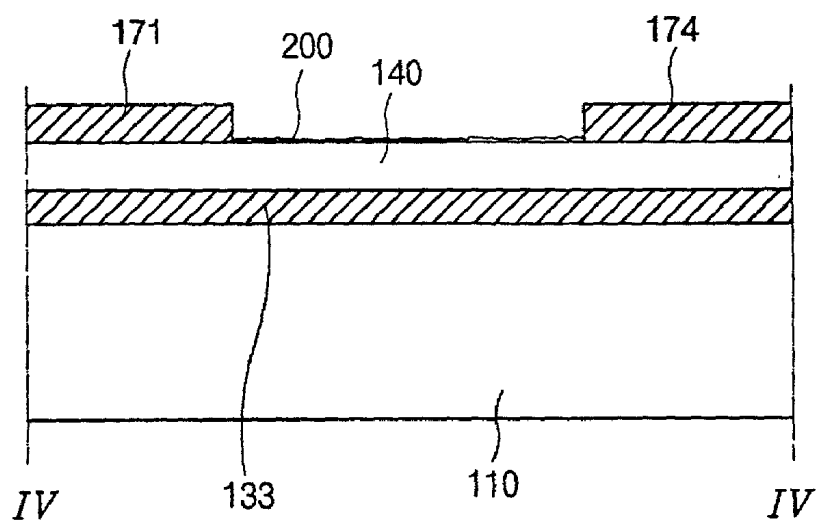


FIG. 5

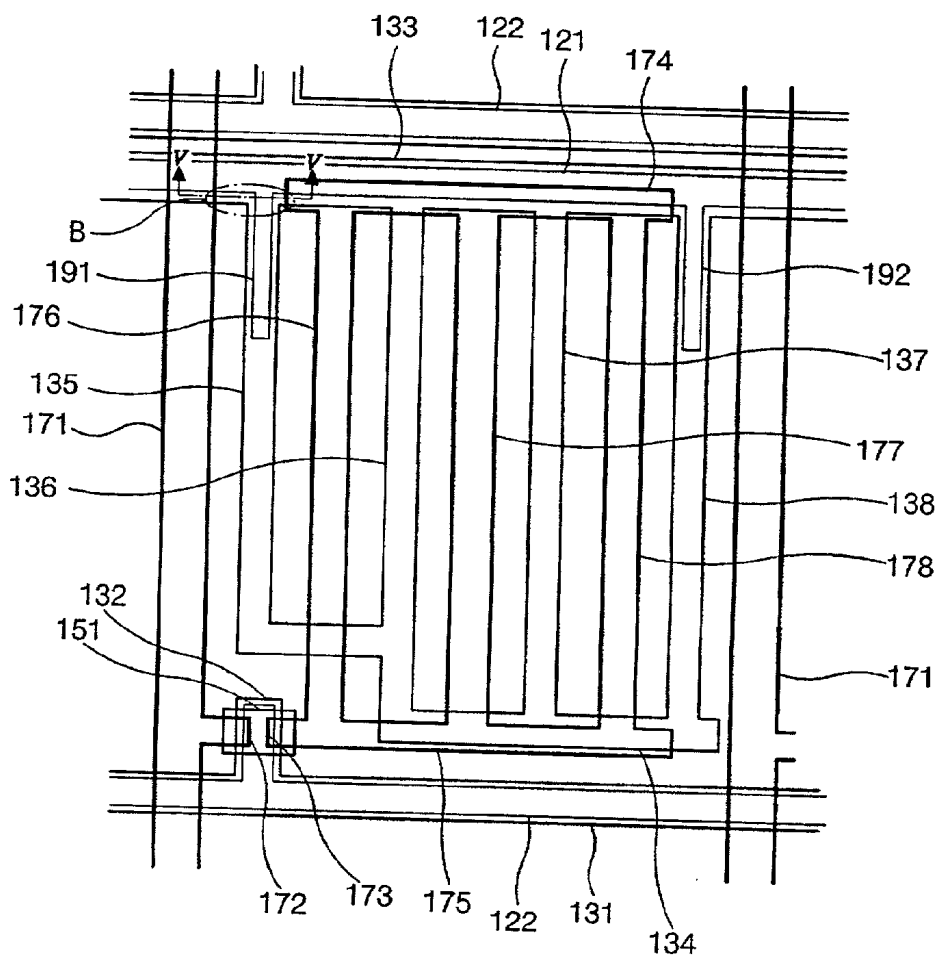


FIG. 6

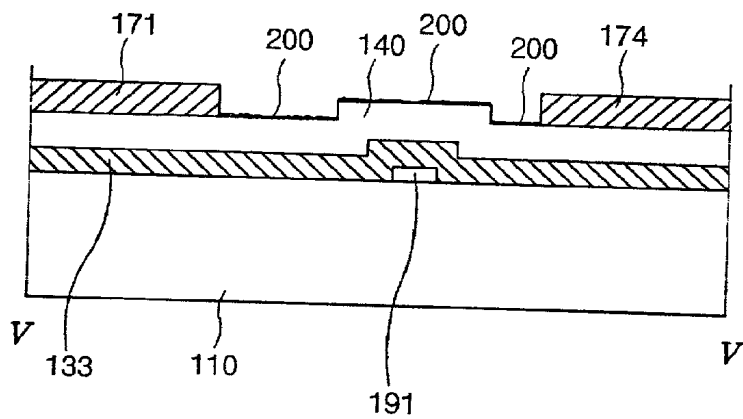


FIG. 7

ARRAY SUBSTRATE FOR IPS MODE LIQUID CRYSTAL DISPLAY DEVICE AND METHOD FOR FABRICATING THE SAME

[0001] This application claims the benefit of Korean Patent Application No. 2000-79356, filed on Dec. 20, 2000 in Korea, which is hereby incorporated by reference as if fully set forth herein.

BACKGROUND OF THE INVENTION

[0002] 1. Field of the Invention

[0003] The present invention relates to a liquid crystal display (LCD) device, and more particularly to an array substrate and a fabricating method thereof for a liquid crystal display device that implements In-Plane Switching (IPS) in which an electric field applied to liquid crystal is generated in a plane parallel to a substrate.

[0004] 2. Discussion of the Related Art

[0005] Until recently, a cathode-ray tube (CRT) has usually been used for displays. However, flat panel displays are becoming more common because of their small depth, low weight and low power consumption. Thin film transistor liquid crystal displays (TFT-LCDs) are currently undergoing development to improve their resolution and to reduce their thickness.

[0006] Generally, a liquid crystal display device includes an upper substrate and a lower substrate each having an electrode thereon and liquid crystal interposed therebetween. If the liquid crystal is aligned by an electric field generated by a voltage applied to the electrodes, desired images can be displayed by a change of transmissivity that depends on the alignment direction of the liquid crystal molecules.

[0007] The general structure of a conventional liquid crystal display device will be described hereinafter with reference to **FIG. 1**. **FIG. 1** is a cross-sectional view illustrating a structure of the conventional liquid crystal display device. As shown in the figure, a gate electrode **21** made of conductive material such as a metal is formed on a lower substrate **10**, i.e., an array substrate. A gate insulating layer **30** including inorganic insulating material such as silicon oxide (SiO_2) or silicon nitride (SiN_x) is formed on the gate electrode **21** and on the lower substrate **10**. An active layer **41** is formed on the gate insulating layer **30** using amorphous silicon. An ohmic contact layer **51, 52** is formed on the active layer **41** using a doped amorphous silicon. Source and drain electrodes **61, 62** made of conductive material are formed on the ohmic contact layer **51, 52** respectively. The gate electrode, the source electrode and the drain electrode constitute a thin film transistor "T". A passivation layer **70** is then formed on the source and drain electrode **61, 62** using inorganic insulating material or organic insulating material. A contact hole **71** through the passivation layer **70** exposes the drain electrode **62** to the air. A pixel electrode **81** made of transparent conductive material is formed on the passivation layer **70**. The pixel electrode **81** contacts the drain electrode **62** through the contact hole **71**. A black matrix **91** is formed beneath a part of an upper substrate **90** corresponding to the thin film transistor "T". A color filter **92** is formed beneath the black matrix **91**. The color filter **92** has sub-color filters Red (R), Green (G) and Blue (B) arranged in a repeated order of R, G, B. A

common electrode **93** made of transparent conductive material is formed beneath the color filter **92**. In addition, a liquid crystal layer **100** is interposed between the upper and lower substrates **90, 10**.

[0008] Liquid crystal molecules are aligned by an electric field generated perpendicularly to the substrates by a voltage applied to the pixel and common electrodes in the conventional liquid crystal display device. Characteristics such as a transmissivity and an aperture ratio are good in the conventional liquid crystal display device and, because the common electrode serves as a ground, destruction of a liquid crystal cell caused by static electricity can be prevented. However, the conventional liquid crystal display device has disadvantages such as a narrow viewing angle. Accordingly, an in-plane switching (IPS) mode liquid crystal display device has been suggested as an alternative to overcome the disadvantages such as a narrow viewing angle.

SUMMARY OF THE INVENTION

[0009] Accordingly, the present invention is directed to an array substrate of in-plane switching (IPS) mode liquid crystal display device and a method for fabricating the same that substantially obviates one or more of problems due to limitations and disadvantages of the related art.

[0010] An advantage of the present invention is to provide an in-plane switching liquid crystal display device that can improve a viewing angle and a production yield.

[0011] Another advantage of the present invention is to provide a fabricating method for an in-plane switching liquid crystal display device.

[0012] Additional features and advantages of the invention will be set forth in the description which follows, and in part will be apparent from the description, or may be learned by practice of the invention. The objectives and other advantages of the invention will be realized and attained by the structure particularly pointed out in the written description and claims hereof as well as the appended drawings.

[0013] To achieve these and other advantages and in accordance with the purpose of the present invention, as embodied and broadly described, an in-plane switching liquid crystal display device includes first and second substrates, a gate line and a data line defining a pixel region on the first substrate, a first line on the first substrate, a common line on the first line, a thin film transistor at a crossing portion between the gate and data lines, a plurality of pixel electrodes on the first substrate, a plurality of common electrodes on the first substrate, a first pixel electrode connecting line on the first substrate, and a liquid crystal layer between the first and second substrates. The first pixel electrode connecting line is partially overlapped with the common line. The in-plane switching liquid crystal display device further includes an auxiliary pattern extended from the first line. The auxiliary pattern is between the first line and the first pixel electrode connecting line. The auxiliary pattern is formed outermost of the common electrode. The in-plane switching liquid crystal display device further comprises a second line underneath the gate line. The thin film transistor includes gate, source and drain electrodes. The common electrode is at the same layer as the gate electrode. The pixel electrode is at the same layer as the source and drain electrodes.

[0014] In another aspect, an in-plane switching liquid crystal display device includes first and second substrates, a gate line and a data line defining a pixel region on the first substrate, a first line on the first substrate, a common line on the first line, a thin film transistor at a crossing portion between the gate and data lines, a plurality of pixel electrodes on the first substrate, a plurality of common electrodes on the first substrate, an auxiliary pattern extended from the first line, and a liquid crystal layer between the first and second substrates. The in-plane switching liquid crystal display device further comprises a first pixel electrode connecting line on the first substrate. The first pixel electrode connecting line is partially overlapped with the common line. The auxiliary pattern is between the first line and the first pixel electrode connecting line. The auxiliary pattern is formed outermost of the common electrode. The in-plane switching liquid crystal display device further includes a second line underneath the gate line. The thin film transistor includes gate, source and drain electrodes. The common electrode is at the same layer as the gate electrode. The pixel electrode is at the same layer as the source and drain electrodes.

[0015] In another aspect, a method for fabricating an in-plane switching liquid crystal display device comprises the steps of forming a gate line and a data line defining a pixel region on a first substrate, forming a first line on the first substrate, forming a common line on the first line, forming a thin film transistor at a crossing portion between the gate and data lines, forming a plurality of pixel electrodes on the first substrate, forming a plurality of common electrodes on the first substrate, forming a first pixel electrode connecting line on the first substrate and forming a liquid crystal layer between the first substrate and a second substrate facing the first substrate. The first pixel electrode connecting line is partially overlapped with the common line. The method for fabricating an in-plane switching liquid crystal display device further comprises the step of forming an auxiliary pattern extended from the first line. The auxiliary pattern is between the first line and the first pixel electrode connecting line. The auxiliary pattern is formed outermost of the common electrode. The method for fabricating an in-plane switching liquid crystal display device further includes the step of forming a second line underneath the gate line. The thin film transistor includes gate, source and drain electrodes. The common electrode is at the same layer as the gate electrode. The pixel electrode is at the same layer as the source and drain electrodes.

[0016] The viewing angle can be improved by introducing the in-plane switching (IPS) mode liquid crystal display device where the common electrode and the pixel electrode are formed on the same substrate and the liquid crystal is aligned by lateral electric field generated by a voltage applied to the common and pixel electrodes. The auxiliary patterns are formed between the first pixel electrode connecting line and the data line parallel to the data line. When the pixel electrode and the data line are formed simultaneously in a same process, there may be residues of conductive material such as a metal. Accordingly, the auxiliary pattern step prevents residues from connecting the pixel electrode to the data line and thus prevents a short circuit.

[0017] It is to be understood that both the foregoing general description and the following detailed description

are exemplary and explanatory and are intended to provide further explanation of the invention as claimed.

BRIEF DESCRIPTION OF THE DRAWINGS

[0018] The accompanying drawings, which are included to provide a further understanding of the invention and are incorporated in and constitute a part of this specification, illustrate embodiments of the invention and together with the description serve to explain the principles of the invention.

[0019] In the drawings:

[0020] FIG. 1 is a cross-sectional view illustrating a structure of a conventional liquid crystal display device;

[0021] FIG. 2 is a plan view illustrating a pixel of an array substrate according to a first embodiment of the present invention;

[0022] FIG. 3 is a cross-sectional view taken along III-III of FIG. 2;

[0023] FIGS. 4A to 4C are cross-sectional views illustrating fabricating sequences of an array substrate according to the present invention;

[0024] FIG. 5 is a cross-sectional view of a portion "A" of FIG. 2;

[0025] FIG. 6 is a plan view illustrating a pixel of an array substrate according to a second embodiment of the present invention; and

[0026] FIG. 7 is a cross-sectional view of a portion "B" of FIG. 6.

DETAILED DESCRIPTION OF THE ILLUSTRATED EMBODIMENTS

[0027] Reference will now be made in detail to the illustrated embodiments of the present invention, which are illustrated in the accompanying drawings.

[0028] FIG. 2 is a plan view illustrating a pixel of an array substrate according to a first embodiment of the present invention and FIG. 3 is a cross-sectional view taken along III-III of FIG. 2. As shown in the figures, first and second lines 121, 122 made of metallic material having a low electric resistance are formed horizontally on a transparent insulating substrate 110. The first and second lines 121, 122 are for reducing the electric resistance of a common line 133 and a gate line 131, respectively. The common line 133 and the gate line 131 are formed on the first line 121 and the second line 122, respectively. A gate electrode 132 extending from the gate line 131 is formed on the second line 122. First, second, third and fourth common electrodes 135, 136, 137, 138 are vertically arranged in the context of FIG. 2. Upper ends of the common electrodes are connected to the common line 133, and a common electrode connecting line 134 is connected to lower ends of the common electrodes 135, 136, 137, 138. A gate insulating layer 140 including inorganic insulating material such as silicon oxide (SiO_2) or silicon nitride (SiN_x), for example, is formed on the substrate 110. A semiconductor layer 151 including amorphous silicon is formed on a part of the gate insulating layer 140 corresponding to the gate electrode 132 and the semiconductor layer 151 serves as an active layer of a thin film transistor. Ohmic contact layers 161, 162 including doped

amorphous silicon are formed on the semiconductor layer **151**. The ohmic contact layers are for reducing an electric resistance caused by a contact between the semiconductor layer **151** and a source and drain electrodes **172**, **173**. A data line **171**, the source electrode **172**, the drain electrode **173**, a first and second pixel electrode connecting lines **174**, **175** and a first, second and third pixel electrodes are formed with conductive material such as a metal on the ohmic contact layer **161**, **162**. The data line **171** defines a pixel region by crossing the gate line **131**. The source electrode **172** extends from the data line **171**. The drain electrode **173** is spaced apart from the source electrode **172**. The gate electrode and the source and drain electrode constitute the thin film transistor. The first, second and third pixel electrodes **176**, **177** and **178** are vertically arranged in an alternating order with the corresponding common electrodes **135**, **136**, **137**, **138**. Upper and lower ends of the pixel electrodes are connected to the horizontal first and second pixel electrode connecting line **174**, **175** respectively. The second pixel electrode connecting line **175** is connected to the drain electrode **173**. A passivation layer may further be formed on the data line **171** and the pixel electrodes **176**, **177**, **178**.

[0029] The present invention can improve a viewing angle by forming the pixel and common electrode on the same substrate, and thus driving liquid crystal molecules by applying a lateral electric field to the liquid crystal. The lateral electric field is generated when a voltage is applied to the pixel and common electrodes.

[0030] A fabricating method for an array substrate for in-plane switching (IPS) mode liquid crystal display device will be described more in detail hereafter with reference to **FIG. 2** and **FIGS. 4A to 4C**. **FIGS. 4A to 4C** are cross-sectional views taken along III-III of **FIG. 2** illustrating fabricating sequences of an array substrate according to the present invention.

[0031] Referring to **FIG. 2** and **FIG. 4A**, horizontal first and second lines **121**, **122** are formed on the transparent insulating substrate **110** by depositing and patterning conductive material such as a metal. The first and second lines **121**, **122** are formed desirably with material having a good adhesive property and a low electric resistance. Then a gate line **131**, a gate electrode **132**, a common line **133**, a common electrode connecting line **134**, and first, second, third and fourth common electrodes **135**, **136**, **137**, **138** are formed by depositing and patterning conductive material such as a metal. The common line **133** and the gate line **131** are formed on the first and second lines **121**, **122**, respectively.

[0032] Referring to **FIG. 2** and **FIG. 4B**, a gate insulating layer **140** covering the gate electrode **132** is formed on the substrate **110**. A semiconductor layer **151** and a doped semiconductor layer **163** are formed over the gate electrode **132** by depositing and patterning amorphous silicon and doped amorphous silicon respectively.

[0033] Referring to **FIG. 2** and **FIG. 4C**, a data line **171**, a source electrode **172**, a drain electrode **173**, first and second pixel electrode connecting lines **174**, **175**, and first, second and third pixel electrodes **176**, **177**, **178** are formed by depositing and patterning conductive metallic material

such as molybdenum (Mo) or chromium (Cr), for example. The ohmic contact layers **161**, **162** is subsequently formed by removing the doped semiconductor layer between the source electrode **172** and the drain electrode **173**.

[0034] As described above, the first and second lines **121**, **122** that are formed under the common line **133** and the gate line **131**, respectively, to reduce the electric resistances prevent signals from being delayed. Because the pixel electrode and the common electrode are formed on the same substrate, and the pixel electrode and the data line are formed simultaneously in the same process, the fabricating process can be simplified according to the present invention. However, when the data line and the pixel electrodes are formed by etching the metallic material, a short circuit may occur because of residue of the metallic material between the data line **171** and the first pixel electrode connecting line **174**.

[0035] **FIG. 5** is a cross-sectional view of a portion "A" of **FIG. 2**. As shown in the figure, a step is formed between the data line **171** and the first pixel electrode connecting line **174** by the first line **121**. The common line **133** is formed on the substrate **110** and the gate insulating layer **140** is formed on the common line **133**. The data line **171** and the first pixel electrode connecting line **174** are formed on the gate insulating layer **140**. The data line **171** and the first pixel electrode connecting line **174** are formed simultaneously in the same process. After the metallic material between the data line **171** and the first pixel electrode connecting line **174** are etched away during the forming process for the data line **171** and the first pixel electrode connecting line **174**, there may exist residues **200** due to a step generated by the first line **121**. The residues **200** may electrically connect the data line **171** to the first pixel electrode connecting line **174** and thus cause a short.

[0036] A second embodiment of the present invention to overcome the short problem will be described hereinafter with reference to **FIG. 6** and **FIG. 7**. **FIG. 6** is a plan view illustrating a pixel of an array substrate according to a second embodiment of the present invention and **FIG. 7** is a cross-sectional view of a portion "B" of **FIG. 6**. The structure of the array substrate of the second embodiment is same as that of the first embodiment except portions of first and fourth common electrodes. As shown in **FIG. 7**, auxiliary patterns **191**, **192** are vertically extended under the first and fourth common electrodes **135**, **138** disposed between the data line **171** and the first pixel electrode connecting line **174**. Accordingly as shown in **FIG. 7**, steps are formed perpendicularly to the steps generated by the first line between the data line **171** and the first pixel electrode connecting line **174**. The steps generated by the auxiliary patterns **191**, **192** prevent residues from connecting the data line **171** to the first pixel electrode connecting line **174** and thus prevent a short circuit.

[0037] It will be apparent to those skilled in the art that various modifications and variation can be made in the fabrication and application of the present invention without departing from the spirit or scope of the invention. Thus, it is intended that the present invention cover the modifications and variations of this invention provided they come within the scope of the appended claims and their equivalents.

What is claimed is:

1. An in-plane switching liquid crystal display device comprising:

first and second substrates;

a gate line and a data line defining a pixel region on the first substrate;

a first conductive line on the first substrate;

a common line on the first conductive line;

a thin film transistor at a crossing portion between the gate and data lines;

a plurality of pixel electrodes on the first substrate;

a plurality of common electrodes on the first substrate;

a first pixel electrode connecting line on the first substrate; and

a liquid crystal layer between the first and second substrates.

2. The device of claim 1, wherein the first pixel electrode connecting line is partially overlapped with the common line.

3. The device of claim 1, further comprising an auxiliary pattern extended from the first conductive line.

4. The device of claim 3, wherein the auxiliary pattern is between the first conductive line and the first pixel electrode connecting line.

5. The device of claim 3, wherein the auxiliary pattern is formed outermost of the common electrodes.

6. The device of claim 1, further comprising a second conductive line underneath the gate line.

7. The device of claim 1, wherein the thin film transistor includes gate, source and drain electrodes.

8. The device of claim 7, wherein the common electrode is at the same layer as the gate electrode.

9. The device of claim 7, wherein the pixel electrode is at the same layer as the source and drain electrodes.

10. An in-plane switching liquid crystal display device comprising:

first and second substrates;

a gate line and a data line defining a pixel region on the first substrate;

a first conductive line on the first substrate;

a common line on the first line;

a thin film transistor at a crossing portion between the gate and data lines;

a plurality of pixel electrodes on the first substrate;

a plurality of common electrodes on the first substrate;

an auxiliary pattern extended from the first conductive line; and

a liquid crystal layer between the first and second substrates.

11. The device of claim 10, further comprising a first pixel electrode connecting line on the first substrate.

12. The device of claim 11, wherein the first pixel electrode connecting line is partially overlapped with the common line.

13. The device of claim 11, wherein the auxiliary pattern is between the first conductive line and the first pixel electrode connecting line.

14. The device of claim 10, wherein the auxiliary pattern is formed outermost of the common electrodes.

15. The device of claim 10, further comprising a second conductive line underneath the gate line.

16. The device of claim 10, wherein the thin film transistor includes gate, source and drain electrodes.

17. The device of claim 16, wherein the common electrode is at the same layer as the gate electrode.

18. The device of claim 16, wherein the pixel electrode is at the same layer as the source and drain electrodes.

19. A method for fabricating an in-plane switching liquid crystal display device comprising:

forming a gate line and a data line defining a pixel region on a first substrate;

forming a first conductive line on the first substrate;

forming a common line on the first conductive line;

forming a thin film transistor at a crossing portion between the gate and data lines;

forming a plurality of pixel electrodes on the first substrate;

forming a plurality of common electrodes on the first substrate;

forming a first pixel electrode connecting line on the first substrate; and

forming a liquid crystal layer between the first substrate and a second substrate facing the first substrate.

20. The method of claim 19, wherein the first pixel electrode connecting line is partially overlapped with the common line.

21. The method of claim 19, further comprising forming an auxiliary pattern extended from the first conductive line.

22. The method of claim 21, wherein the auxiliary pattern is between the first conductive line and the first pixel electrode connecting line.

23. The method of claim 19, wherein the auxiliary pattern is formed outermost of the common electrodes.

24. The method of claim 19, further comprising a second conductive line underneath the gate line.

25. The method of claim 19, wherein the thin film transistor includes gate, source and drain electrodes.

26. The method of claim 25, wherein the common electrode is at the same layer as the gate electrode.

27. The method of claim 25, wherein the pixel electrode is at the same layer as the source and drain electrodes.

* * * * *

专利名称(译)	用于IPS模式液晶显示装置的阵列基板及其制造方法		
公开(公告)号	US20020167633A1	公开(公告)日	2002-11-14
申请号	US10/020894	申请日	2001-12-19
[标]申请(专利权)人(译)	朴贞KI CHO JAE SUNG		
申请(专利权)人(译)	朴贞-KI CHO JAE-SUNG		
当前申请(专利权)人(译)	LG DISPLAY CO. , LTD.		
[标]发明人	PARK JEONG KI CHO JAE SUNG		
发明人	PARK, JEONG-KI CHO, JAE-SUNG		
IPC分类号	G02F1/136 G02F1/1343		
CPC分类号	G02F1/134363		
优先权	1020000079356 2000-12-20 KR		
其他公开文献	US6950164		
外部链接	Espacenet USPTO		

摘要(译)

面内切换 (IPS) 模式液晶显示装置的阵列基板包括从公共线下方的第一导线延伸的辅助图案，以防止由用于形成数据线的金属材料的残留物引起的短路。像素电极。

